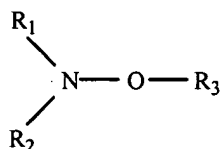


IN THE CLAIMS:

Rewrite the pending claims and add new claims as follows:

1. (Original) A method of removing a resist from a substrate by contacting a substrate having a resist thereon with an aqueous remover wherein said remover contains hydroxylamine and at least one alkanolamine wherein said hydroxylamine and said alkanolamine are present in sufficient amounts to remove a resist from a substrate.
2. (Original) The method of claim 1 wherein the resist includes a polyimide.
3. (Original) The method of claim 1 wherein the resist includes resist that has been exposed to a process selected from plasma etching, reactive ion etching and ion milling.
4. (Original) The method of claim 1 wherein said remover further includes a chelating agent.
5. (Currently amended) The method of claim 1 wherein said hydroxylamine and said at least one alkanolamine solvent are maintained separately and are combined at the process location where said remover contacts said resist.
6. (Currently amended) The method of claim 5 wherein a chelating agent is maintained separately and combined with ~~added to the remover after combining~~ said hydroxylamine and said at least one alkanolamine at said process location.
7. (Original) The method of claim 1 wherein said remover contacts said resist during the fabrication of a submicron integrated circuit.
8. (Currently amended) The method of claim 1 wherein said hydroxylamine is present in an amount from at least about 2.5% to about ~~45~~25% by weight neat.
9. (Original) The method of claim 8 wherein said remover further contains a chelating agent.
10. (Original) The method of claim 9 wherein said remover further contains at least one polar solvent.

11. (Original) The method of claim 8 wherein said at least one alkanolamine is selected from the group consisting of monoamines, diamines and triamines.
12. (Currently amended) A method of removing a resist from a substrate by contacting a substrate having a resist thereon with an aqueous remover wherein said remover comprises from about 2.5% to about ~~45~~25% by weight neat hydroxylamine, at least one alkanolamine, and at least one polar solvent wherein said remover contacts said substrate having a resist thereon after a process of etching.
13. (Currently amended) The method of claim 12 wherein said ~~contacting occurs after the process of etching~~ remover comprises about 8.75% to about 20% by weight neat hydroxylamine, at least one alkanolamine selected from the group consisting of monoamines, diamines, and triamines, at least one polar solvent, and a chelating agent.
14. (Original) The method of claim 1 wherein the aqueous remover contains at least about 70% water.
15. (Original) The method of claim 12 wherein the aqueous remover contains at least about 70% water.
16. (Original) The method of claim 12 wherein said remover further includes a chelating agent.
17. (Original) The method of claim 4 wherein said chelating agent is an organic acid.
18. (Original) The method of claim 16 wherein said chelating agent is an organic acid.
19. (Currently amended) A method of removing a resist from a substrate by contacting a substrate having a resist thereon with an aqueous remover wherein said remover comprises a hydroxylamine of the formula:



wherein R₁, and R₂, ~~and R₃~~ are independently hydrogen; a hydroxyl group; optionally a substituted C₁-C₆ straight, branched or cyclo alkyl, alkenyl, or alkynyl group; optionally a

substituted acyl group, straight or branched alkoxy group, amidyl group, carboxyl group, alkoxyalkyl group, alkylamino group, alkylsulfonyl group, or sulfonic acid group, or the salt of such compounds; and R_3 is hydrogen; optionally a substituted C_1 - C_6 straight, branched or cyclo alkyl, alkenyl, or alkynyl group; optionally a substituted acyl group, straight or branched alkoxy group, amidyl group, carboxyl group, alkoxyalkyl group, alkylamino group, alkylsulfonyl group, or sulfonic acid group, or the salt of such compounds; at least one alkanolamine selected from the group consisting of monoamines, diamines and triamines; at least one polar solvent; and at least one chelating agent.

20. (Original) The method of claim 19 wherein said contacting occurs after the process of etching.